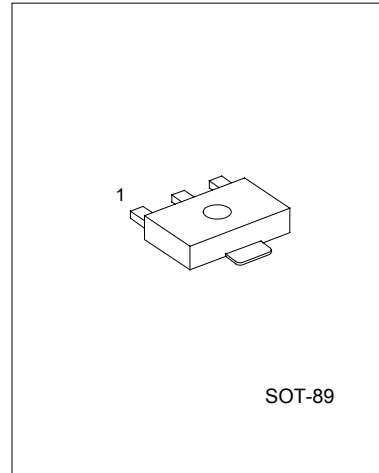


UTC2SB766A PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY OUTPUT AMPLIFICATION

FEATURES

- *Large collector power dissipation P_c .
- *Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-60	V
Collector-Emitter Voltage	V_{CE0}	-50	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_c	-1	A
Peak Collector Current	I_{cp}	-1.5	A
Collector Power Dissipation	P_c^*	1	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

*Printed circuit board :Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion.

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Voltage	V_{CB0}	$I_c = -10\ \mu\text{A}, I_E = 0$	-60			V
Collector Emitter Voltage	V_{CE0}	$I_c = -2\text{mA}, I_B = 0$	-50			V
Emitter Base Voltage	V_{EB0}	$I_E = -10\ \mu\text{A}, I_C = 0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-0.1	μA
DC Current Transfer Ratio	h_{FE1}	$V_{CE} = -10\text{V}, I_c = -500\text{mA}^*$	85		340	
	h_{FE2}	$V_{CE} = -5\text{V}, I_c = -1\text{A}^*$	50			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -500\text{mA}, I_B = -50\text{mA}^*$		-0.2	-0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -500\text{mA}, I_B = -50\text{mA}^*$		-0.85	-1.2	V
Transition Frequency	f_T	$V_{CB} = -10\text{V}, I_E = 50\text{mA}, f = 200\text{MHz}$		200		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		20	30	pF

*Pulse measurement

CLASSIFICATION OF h_{FE1}

RANK	Q	R	S
RANGE	85-170	120-240	170-340

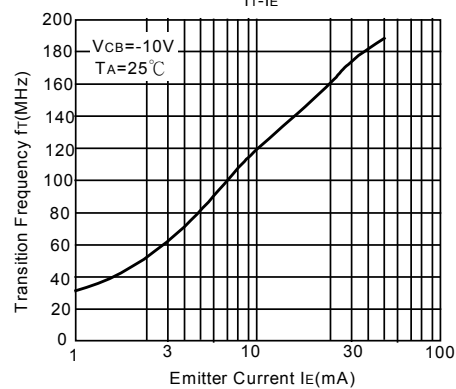
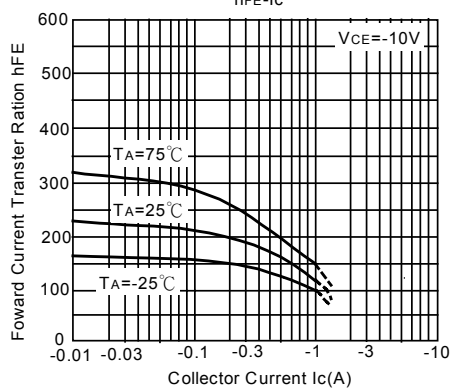
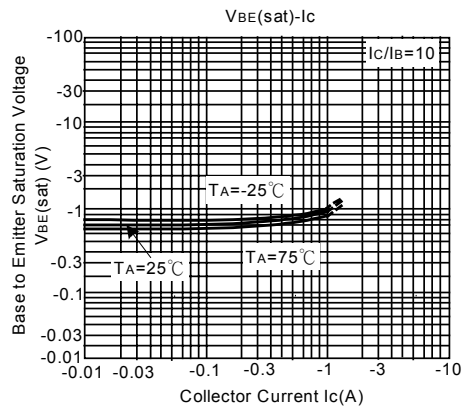
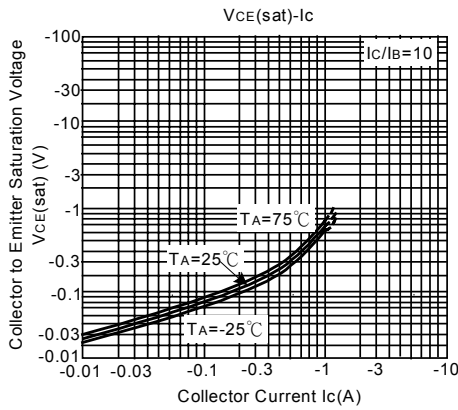
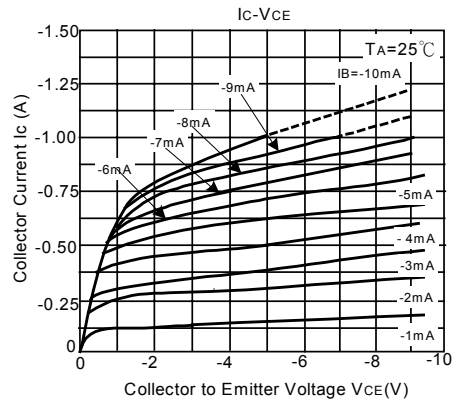
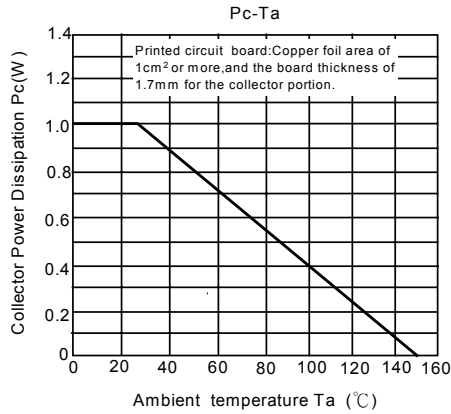
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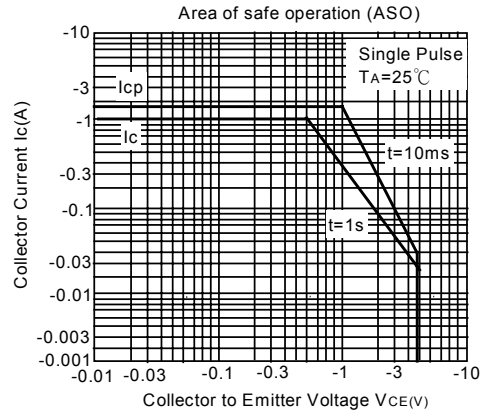
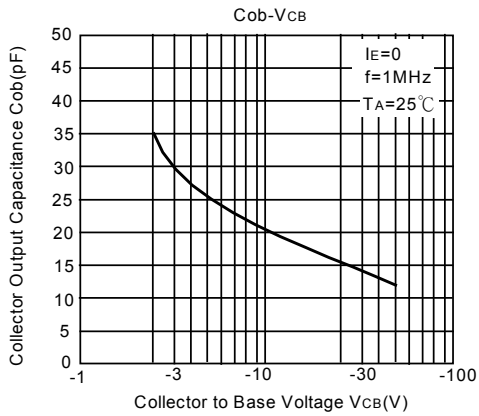
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UTC2SB766A PNP EPITAXIAL SILICON TRANSISTOR

ELECTRICAL CHARACTERISTICS CURVES





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